



A1A:50.XX

VOLTAGE RATINGS

Part Number	V _{RRM} , V _R (V) Max. rep. peak reverse voltage		V _{RSM} , V _R (V) Max. non- rep. peak reverse voltage
	T _J = 0 to 180°C	T _J = -40 to 0°C	T _J = 25 to 180°C
A1A:50.02	200	200	300
A1A:50.04	400	400	500
A1A:50.06	600	600	700
A1A:50.08	800	800	900
A1A:50.10	1000	1000	1100
A1A:50.12	1200	1200	1300
A1A:50.14	1400	1400	1500
A1A:50.16	1600	1600	1700

This datasheet applies to:

**Metric thread: A1A:50.XX,
A1B:50.XX**

**Inch thread: A2A:50.XX,
A2B:50.XX**

MAXIMUM ALLOWABLE RATINGS

PARAMETER	VALUE	UNITS	NOTES
T _J Junction Temperature	-40 to 180	°C	-
T _{stg} Storage Temperature	-40 to 180	°C	-
I _{F(AV)} Max. Av. current @ Max. T _C	50	A	180° half sine wave
	125	°C	
I _{F(RMS)} Nom. RMS current	95	A	-
I _{FSM} Max. Peak non-rep. surge current	640	A	50 Hz half cycle sine wave Initial T _J = 180° C, rated V _{RRM} applied after surge.
	697		60 Hz half cycle sine wave
	762		50 Hz half cycle sine wave Initial T _J = 180° C, no voltage applied after surge.
	830		60 Hz half cycle sine wave
I ² t Max. I ² t capability	1.87	kA ² s	t = 10ms Initial T _J = 180° C, rated V _{RRM} applied after surge.
	2.04		t = 8.3 ms
	2.65		t = 10ms Initial T _J = 180° C, no voltage applied after surge.
	2.89		t = 8.3 ms
I ² t ^{1/2} Max. I ² t ^{1/2} capability	20	kA ² s ^{1/2}	Initial T _J = 180° C, no voltage applied after surge. I ² t for time t _x = I ² t ^{1/2} * t _x ^{1/2} . (0.1 < t _x < 10ms).
F Mounting Force	4(~30)	N.m(Lbf.in)	-



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CHARACTERISTICS

PARAMETER	MIN.	TYP.	MAX.	UNITS	TEST CONDITIONS
V_{FM} Peak forward voltage	---	1.35	1.50	V	Initial $T_J = 25^\circ\text{C}$, sinusoidal wave, $I_{peak} = 157\text{A}$.
$V_{F(TO)1}$ Low-level threshold	---	---	0.88	V	$T_J = 180^\circ\text{C}$
$V_{F(TO)2}$ High-level threshold	---	---	1.02	V	Av. power = $V_{F(TO)} * I_{F(AV)} + r_F * [I_{F(RMS)}]^2$
r_{F1} Low-level resistance	---	---	2.50	m	Use low values for $I_{FM} < I_{F(AV)}$
r_{F2} High-level resistance	---	---	1.53	m	
I_{RM} Peak reverse current	---	---	4.00	mA	$T_J = 180^\circ\text{C}$. Max. Rated V_{RRM}
R_{thJC} Thermal resistance, junction-to-case	---	---	0.85	$^\circ\text{C/W}$	DC operation
	---	---	1.00	$^\circ\text{C/W}$	180° sine wave
	---	---	1.20	$^\circ\text{C/W}$	120° rectangular wave
R_{thCS} Thermal resistance, case-to-sink	---	---	0.20	$^\circ\text{C/W}$	Mtg. Surface smooth, flat and greased. Single side.
wt Weight	---	30(1.06)	---	g(oz.)	---
Case Style	DO-203AB (DO-5)			JEDEC	---

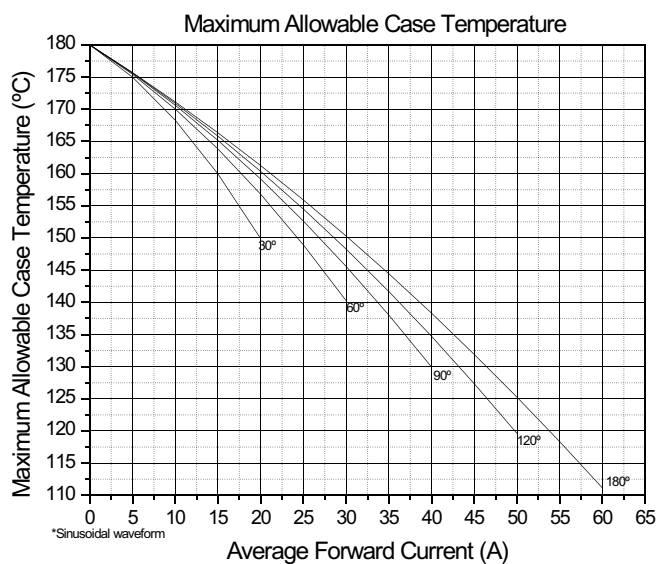


Fig. 1 - Current Ratings Characteristics

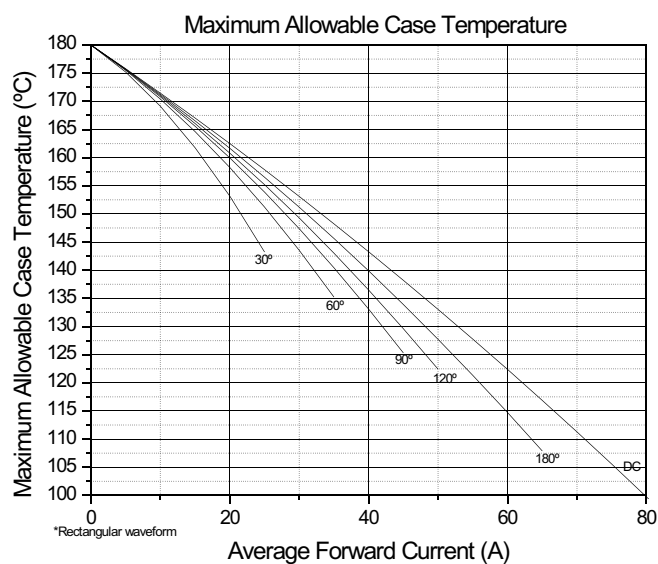


Fig. 2 - Current Ratings Characteristics



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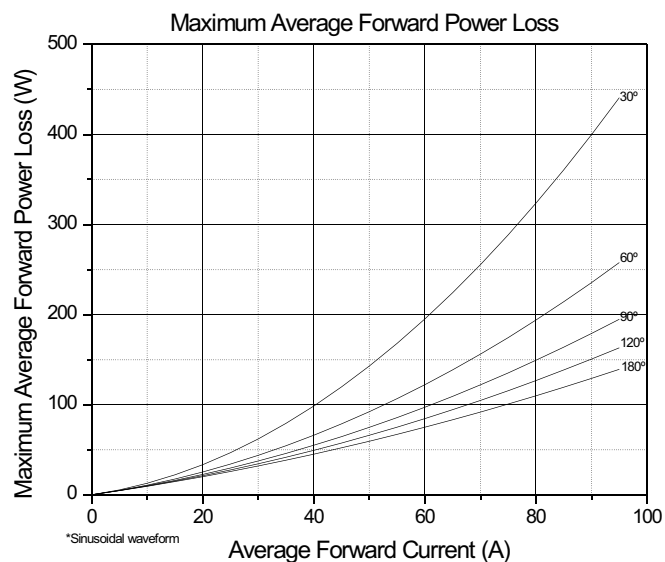


Fig. 3 - On-State Power Loss Characteristics



Fig. 4 - On-State Power Loss Characteristics

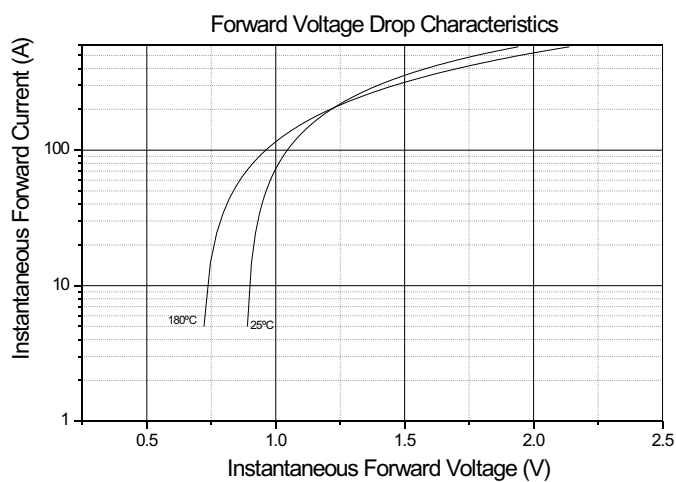


Fig. 5 - Forward Voltage Drop Characteristics

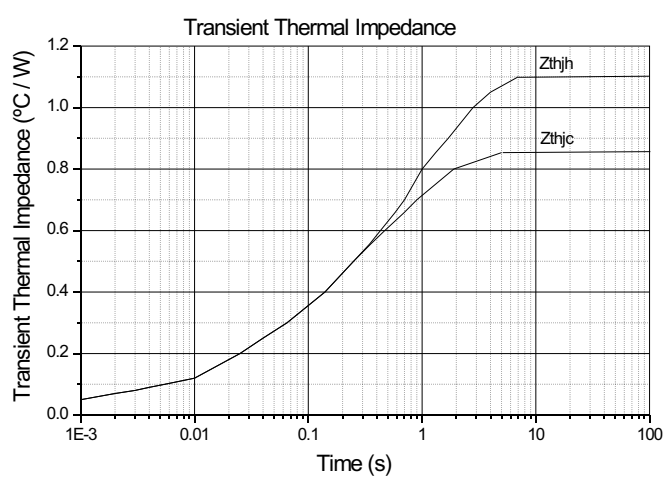


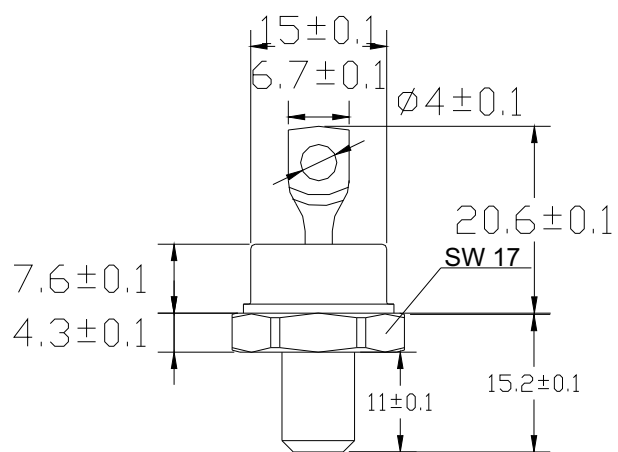
Fig. 6 - Transient Thermal Impedance



AEGIS
SEMICONDUCTORES LTDA.

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DO-5



M8 x 1.25
1/4" UNF 2A

Fig. 7 - Outline Characteristics